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## Amendments to the claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

## Listing of claims:

Claims 1-8 (canceled)

Claim 9 (currently amended): A window ball grid array (WBGA) semiconductor package, comprising:

a core layer having a first surface and an opposite second surface, and a through hole penetrating through the core layer, wherein the second surface is formed with a plurality of wire-bonding portions around the through hole, a plurality of ball-bonding portions, and a plurality of intended-exposing regions around the wire-bonding portions;

at least one chip mounted on the first surface of the core layer and over the through hole, with a portion of the chip exposed via the through hole;

a solder mask layer applied over the second surface of the core layer with the ballbonding portions being exposed, wherein the solder mask layer is formed with an opening for exposing the through hole, the wire-bonding portions, and the intended-exposing regions;

a plurality of bonding wires which penetrate through the through hole and electrically connect the chip to the wire-bonding portions;

a first encapsulation body formed on the first surface of the core layer for encapsulating the chip;

a second encapsulation body formed on the second surface of the core layer for encapsulating the bonding wires and the intended-exposing regions, wherein a thickness of the second encapsulation body covering the intended-exposing regions is substantially equal to that of the solder mask layer; and

a plurality of solder balls deposited on the ball-bonding portions.

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Claim 10 (original): The WBGA semiconductor package of claim 9, wherein a width of the intended-exposing region is of a range from 0.2 to 0.8 mm.

Claim 11 (original): The WBGA semiconductor package of claim 10, wherein the width of the intended-exposing region is 0.4 mm.

Claim 12 (original): The WBGA semiconductor package of claim 9, wherein the intendedexposing regions are located adjacent to the wire-bonding portions.

Claim 13 (original): The WBGA semiconductor package of claim 9, wherein the opening of the solder mask layer is larger in width than a mold cavity of a mold used for forming the second encapsulation body.

Claim 14 (canceled)

Claim 15 (original): The WBGA semiconductor package of claim 9, further comprising: a layer of patterned conductive traces applied between the second surface of the core layer and the solder mask layer.

Claim 16 (original): The WBGA semiconductor package of claim 9, further comprising: another solder mask layer applied between the first surface of the core layer and the chip.

Claim 17 (original): A chip carrier used in a window ball grid array (WBGA) semiconductor package, comprising:

a core layer having a first surface and an opposite second surface, and a through hole penetrating through the core layer;

a conductive trace layer applied over the second surface of the core layer, and formed with a plurality of wire-bonding portions around the through hole, a plurality of ball-bonding portions, and a plurality of intended-exposing regions around the wire-bonding portions; and

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a solder mask layer applied over the conductive trace layer with the ball-bonding portions being exposed, and formed with an opening for exposing the through hole, the wire-bonding portions, and the intended-exposing regions.

Claim 18 (original): The chip carrier of claim 17, wherein a width of the intended-exposing region is of a range from 0.2 to 0.8 mm.

Claim 19 (original): The chip carrier of claim 18, wherein the width of the intended-exposing region is 0.4 mm.

Claim 20 (original): The chip carrier of claim 17, further comprising: another solder mask layer applied over the first surface of the core layer.

Claim 21 (new): A chip carrier used in a window ball grid array (WBGA) semiconductor package, comprising:

a core layer having a first surface and an opposite second surface, and a through hole penetrating through the core layer;

a conductive trace layer applied over the second surface of the core layer, and formed with a plurality of wire-bonding portions around the through hole, a plurality of ball-bonding portions, and a plurality of intended-exposing regions around the wire-bonding portions; and

a solder mask layer applied over the conductive trace layer with the ball-bonding portions being exposed, and formed with an opening for exposing the through hole, the wire-bonding portions, and the intended-exposing regions, wherein an encapsulation body in the semiconductor package for covering the intended-exposing regions is substantially equal in thickness to the solder mask layer.

Claim 22 (new): The chip carrier of claim 21, wherein a width of the intended-exposing region is of a range from 0.2 to 0.8 mm.

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Claim 23 (new): The chip carrier of claim 22, wherein the width of the intended-exposing region is 0.4 mm.

Claim 24 (new): The chip carrier of claim 21, further comprising: another solder mask layer applied over the first surface of the core layer.